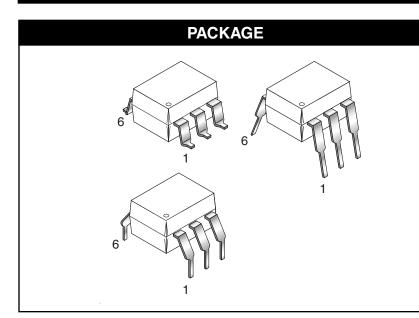
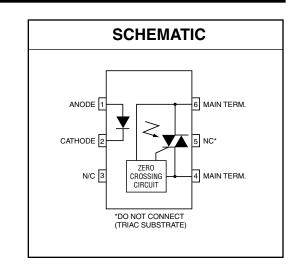


MOC3061-M MOC3062-M MOC3063-M MOC3162-M MOC3163-M





DESCRIPTION

The MOC306X-M and MOC316X-M devices consist of a GaAs infrared emitting diode optically coupled to a monolithic silicon detector performing the function of a zero voltage crossing bilateral triac driver. They are designed for use with a triac in the interface of logic systems to equipment powered from 115/240 VAC lines, such as solid-state relays, industrial controls, motors, solenoids and consumer appliances, etc.

FEATURES

- Simplifies logic control of 115/240 VAC power
- Zero voltage crossing
- dv/dt of 1000 V/µs guaranteed (MOC316X-M),
 600 µs guaranteed (MOC306X-M)
- VDE recognized (File # 94766)
- ordering option V (e.g., MOC3063V-M)
- Underwriters Laboratories (UL) recognized (File #E90700, volume 2)

APPLICATIONS

- Solenoid/valve controls
- Static power switches
- Temperature controls
- AC motor starters
- Lighting controls
- AC motor drives
- E.M. contactors
- Solid state relays



MOC3061-M	MOC3062-M	MOC3063-M	MOC3162-M	MOC3163-M

ABSOLUTE MAXIMUM RATINGS (T _A = 25° C unless	otherwise n	oted)		
Parameters	Symbol	Device	Value	Units
TOTAL DEVICE				
Storage Temperature	T _{STG}	All	-40 to +150	°C
Operating Temperature	T _{OPR}	All	-40 to +85	°C
Lead Solder Temperature	T _{SOL}	All	260 for 10 sec	°C
Junction Temperature Range	ТJ	All	-40 to +100	°C
Isolation Surge Voltage ⁽⁴⁾ (peak AC voltage, 60Hz, 1 sec duration)	V _{ISO}	All	7500	Vac(pk)
Total Device Power Dissipation @ 25°C	Р	A.II.	250	mW
Derate above 25°C	PD	All	2.94	mW/°C
EMITTER				
Continuous Forward Current	I _F	All	60	mA
Reverse Voltage	V _R	All	6	V
Total Power Dissipation 25°C Ambient	Р	A.II.	120	mW
Derate above 25°C	PD	All	1.41	mW/°C
DETECTOR				
Off-State Output Terminal Voltage	V _{DRM}	All	600	V
Peak Repetitive Surge Current (PW = 100 µs, 120 pps)	I _{TSM}	All	1	Α
Total Power Dissipation @ 25°C Ambient		A.II.	150	mW
Derate above 25°C	PD	All	1.76	mW/°C



SEMICONDUCTOR®

MOC3061-M MOC3062-M MOC3063-M MOC3162-M MOC3163-M

ELECTRICAL CHARACTERISTICS (TA = 25°C Unless otherwise specified)

INDIVIDUAL COMPONENT CHARACTERISTICS

Parameters	Test Conditions	Symbol	Device	Min	Тур*	Max	Units
EMITTER							
Input Forward Voltage	I _F = 30 mA	V _F	All		1.3	1.5	V
Reverse Leakage Current	V _R = 6 V	I _R	All		0.005	100	μA
DETECTOR							
Peak Blocking Current Either Direction	$V_{-} = 600V_{-} = 0$ (pote 1)		MOC316X-M		10	100	54
Peak Blocking Current, Either Direction	V _{DRM} = 600V, I _F = 0 (note 1)	DRM1	MOC306X-M		10	500	nA
Critical Rate of Rise of Off-State Voltage	I _F = 0 (figure 9, note 3)	dv/dt	MOC306X-M	600	1500		V/µs
Cilical hate of hise of OII-State voltage	F = 0 (ligure 9, fible 3)	uv/ut	MOC316X-M	1000			v/µs

TRANSFER CHARACTERISTICS ($T_A = 25^{\circ}C$ Unless otherwise specified.)							
DC Characteristics	Test Conditions	Symbol	Device	Min	Тур*	Max	Units
			MOC3061-M			15	mA
LED Trigger Current (rated I _{FT})	main terminal Voltage = 3V (note 2)	I _{FT}	MOC3062-M/ MOC3162-M	C3162-M		10	
			MOC3063-M/ MOC3163-M			10 5	
Peak On-State Voltage, Either Direction	I _{TM} = 100 mA peak, I _F = rated I _{FT}	V _{TM}	All		1.8	3	V
Holding Current, Either Direction		I _H	All		500		μA

ZERO CROSSING CHARACTERISTICS							
Characteristics	Test Conditions	Symbol	Device	Min	Тур*	Мах	Units
Inhibit Voltage (MT1-MT2 voltage			MOC3061-M/2M/3M		12	20	
above which device will not trigger)	I _F = Rated I _{FT}	V _{INH}	MOC3162-M/3M		12	15	V
Leakage in Inhibited State	I _F = Rated I _{FT} , V _{DRM} = 600V, off state	I _{DRM2}	All		150	500	μA

ISOLATION CHARACTERISTICS							
Characteristics	Test Conditions	Symbol	Device	Min	Тур*	Max	Units
Isolation Voltage	f = 60 Hz, t = 1 sec	V _{ISO}	All	7500			V

*Typical values at $T_A = 25^{\circ}C$

Notes

1. Test voltage must be applied within dv/dt rating.

 All devices are guaranteed to trigger at an I_F value less than or equal to max I_{FT}. Therefore, recommended operating I_F lies between max I_{FT} (15 mA for MOC3061-M, 10 mA for MOC3062-M & MOC3162-M, 5 mA for MOC3063-M & MOC3163-M) and absolute max I_F (60 mA).

3. This is static dv/dt. See Figure 9 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.

4. Isolation surge voltage, V_{ISO}, is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

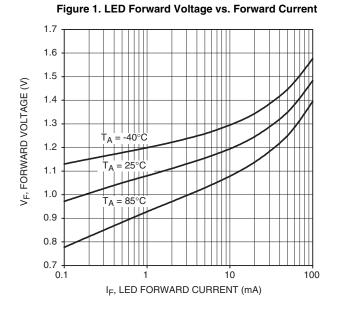


MOC3061-M N

MOC3062-M

MOC3063-M MOC3162-M

MOC3163-M



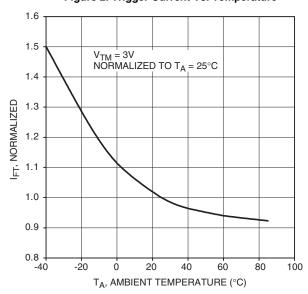
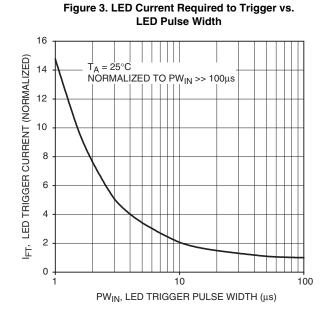
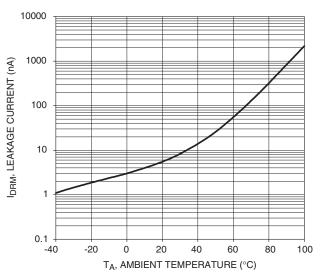


Figure 2. Trigger Current Vs. Temperature

Figure 4. Leakage Current, IDRM vs. Temperature







MOC3061-M

MOC3062-M

MOC3063-M MOC3162-M MOC3163-M

Figure 6. On-State Characteristics

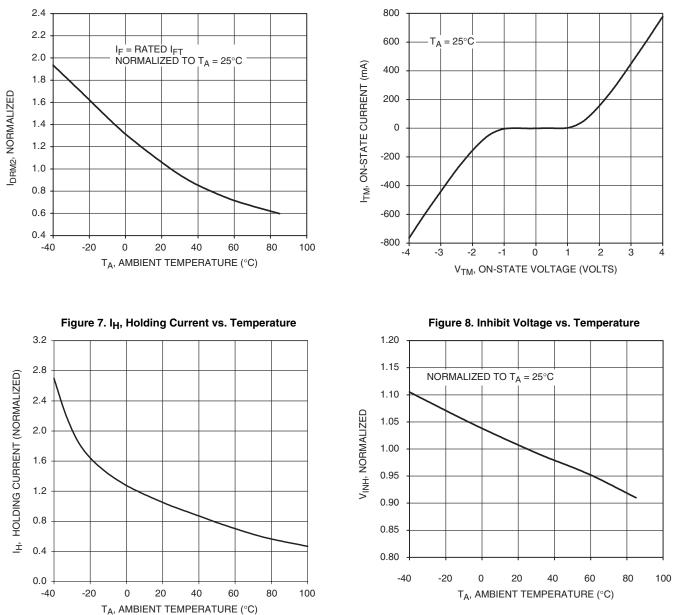


Figure 5. IDRM2, Leakage in Inhibit State vs. Temperature



MOC3061-M MOC3062-M MOC3063-M MOC3162-M MOC3163-M

- 1. 100x scope probes are used, to allow high speeds and voltages.
- 2. The worst-case condition for static dv/dt is established by triggering the D.U.T. with a normal LED input current, then removing the current. The variable vernier resistor combined with various capacitor combinations allows the dv/dt to be gradually increased until the D.U.T. continues to trigger in response to the applied voltage pulse, even after the LED current has been removed. The dv/dt is then decreased until the D.U.T. stops triggering. τ_{RC} is measured at this point and recorded.

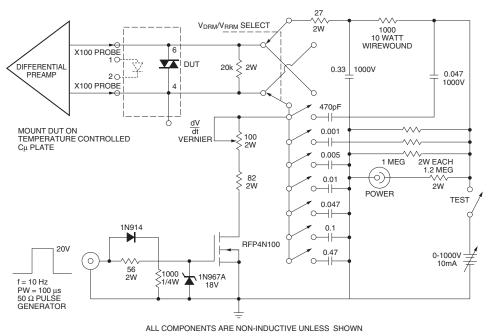


Figure 9. Circuit for Static $\frac{dV}{dt}$ Measurement of Power Thyristors

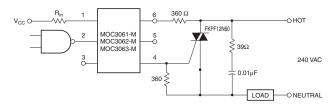
BASIC APPLICATIONS

Typical circuit for use when hot line switching is required. In this circuit the "hot" side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.

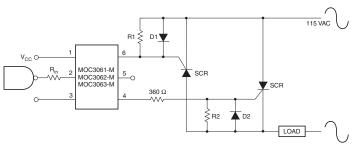
 R_{in} is calculated so that I_F is equal to the rated I_{FT} of the part, 15 mA for the MOC3061-M, 10 mA for the MOC3062-M, or 5 mA for the MOC3063-M. The 39 ohm resistor and 0.01 μF capacitor are for snubbing of the triac and is often, but not always, necessary depending upon the particular triac and load used.

Suggested method of firing two, back-to-back SCR's with a Fairchild triac driver. Diodes can be 1N4001; resistors, R1 and R2, are optional 330 ohm.

Note: This optoisolator should not be used to drive a load directly. It is intended to be a trigger device only.



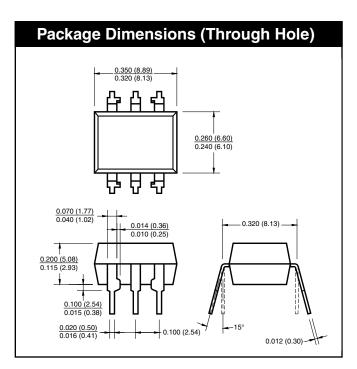




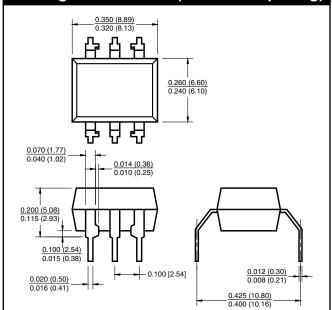




MOC3061-M MOC3062-M MOC3063-M MOC3162-M MOC3163-M

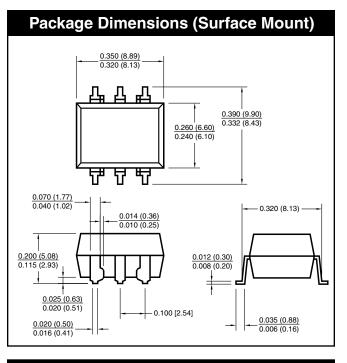


Package Dimensions (0.4" Lead Spacing)

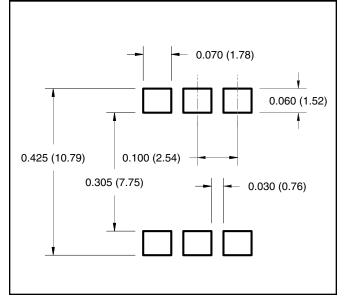


NOTE

All dimensions are in inches (millimeters)



Recommended Pad Layout for Surface Mount Leadform



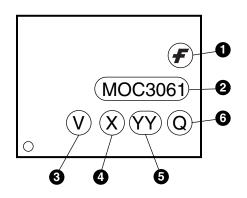


MOC3061-M MOC3062-M MOC3063-M MOC3162-M MOC3163-M

ORDERING INFORMATION

Option	Order Entry Identifier	Description
S	S	Surface Mount Lead Bend
SR2	SR2	Surface Mount; Tape and reel
Т	Т	0.4" Lead Spacing
V	V	VDE 0884
TV	TV	VDE 0884, 0.4" Lead Spacing
SV	SV	VDE 0884, Surface Mount
SR2V	SR2V	VDE 0884, Surface Mount, Tape & Reel

MARKING INFORMATION

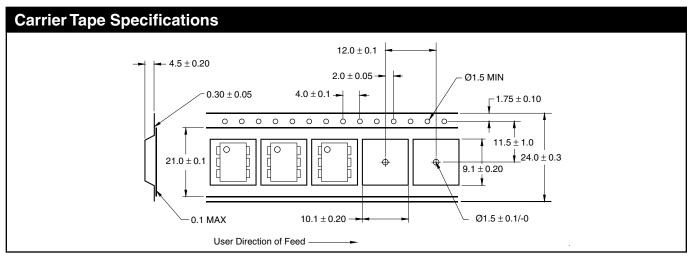


Definitions					
1	Fairchild logo				
2	Device number				
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)				
4	One digit year code, e.g., '3'				
5	Two digit work week ranging from '01' to '53'				
6	Assembly package code				

*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.

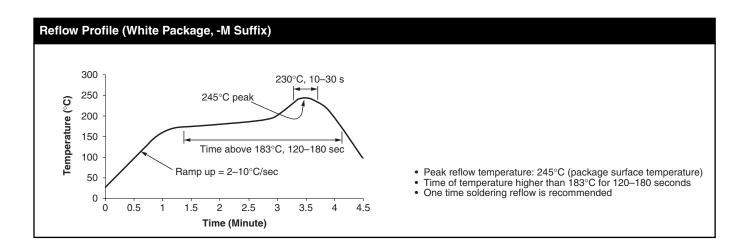


MOC3061-M MOC3062-M MOC3063-M MOC3162-M MOC3163-M



NOTE

All dimensions are in inches (millimeters)





SEMICONDUCTOR®

6-PIN DIP ZERO-CROSS PHOTOTRIAC DRIVER OPTOCOUPLER (600V PEAK)

MOC3061-M MOC3062-M MOC3063-M MOC3162-M MOC3163-M

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.